

FJNS4201R

Switching Application (Bias Resistor Built In)

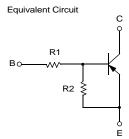
- Switching circuit, Inverter, Interface circuit, Driver Circuit
- Built in bias Resistor (R₁=4.7K Ω , R₂=4.7K Ω)
- Complement to FJNS3201R



PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	-50	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-10	V
I _C	Collector Current	-100	mA
P _C	Collector Power Dissipation	300	mW
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 ~ 150	°C



Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_{C} = -10\mu A, I_{E} = 0$	-50			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = -100 \mu A, I_B = 0$	-50			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = -40V, I_{E} = 0$			-0.1	μΑ
h _{FE}	DC Current Gain	V_{CE} = -5V, I_{C} = -10mA	20			
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = -10mA, I _B = -0.5mA			-0.3	V
f _T	Current Gain Bandwidth Product	V_{CE} = -10V, I_{C} =-5mA		200		MHz
C _{ob}	Output Capacitance	V _{CB} = -10V, I _E =0 f=1.0MHz		5.5		pF
V _I (off)	Input Off Voltage	V_{CE} = -5V, I_{C} = -100 μ A	-0.5			V
V _I (on)	Input On Voltage	V_{CE} = -0.3V, I_{C} = -20mA			-3	V
R ₁	Input Resistor		3.2	4.7	6.2	ΚΩ
R ₁ /R ₂	Resistor Ratio		0.9	1	1.1	

Typical Characteristics

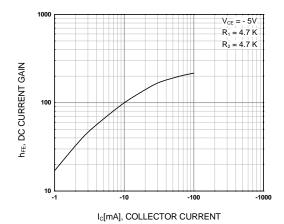


Figure 1. DC current Gain

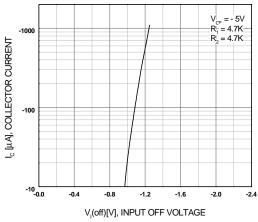
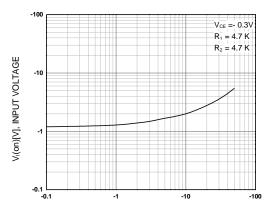


Figure 3. Input Off Voltage



 $I_{\text{C}}[\text{mA}]$, COLLECTOR CURRENT

Figure 2. Input On Voltage

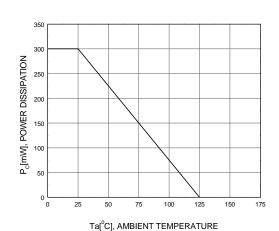
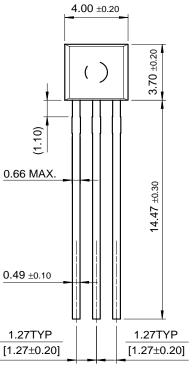
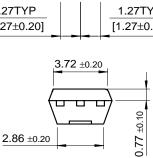
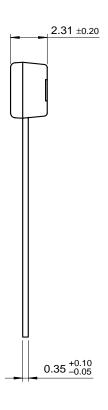


Figure 4. Power Derating

TO-92S







Dimensions in Millimeters

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